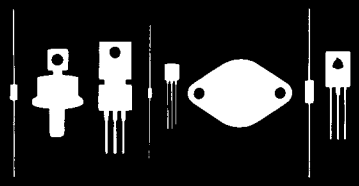
Central
Semiconductor Corp.
145 Adams Avenue
Hauppauge, New York 11788



MJE370 PNP
MJE520 NPN

SILICON COMPLEMENTARY
POWER TRANSISTORS

JEDEC TO-126 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MJE370, MJE520 types are Complementary Silicon Power Transistors designed for use in general purpose amplifier and switching applications.

MAXIMUM RATINGS (T_C=25°C)

	SYMBOL		UNIT
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	4.0	V
Collector Current	I_C	3.0	A
Collector Current (PEAK)	I_{CM}	7.0	A
Power Dissipation	P_D	25	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 TO +150	°C
Thermal Resistance	θ_{JC}	5.0	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_{CBO}	V_{CB}=30V		100	μA
I_{EBO}	V_{EB}=4.0V		100	μA
BV_{CEO}	I_C=100mA	30		V
h_{FE}	V_{CE}=1.0V, I_C=1.0A	25		

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